

# Silicon Switching Diode

**1N914**  
or  
**1N914-1**

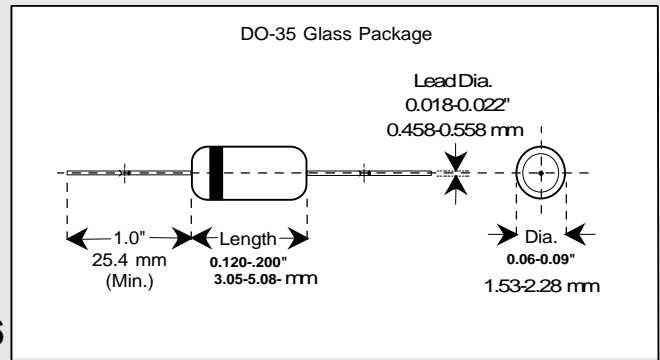
# DO-35 Glass Package

## Applications

Used in general purpose applications, where performance and switching speed are important.

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to SCDs



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	$I_{Avg}$	75	mAmps
Continuous Forward Current	$I_{Fdc}$	300	mAmps
Peak Surge Current ( $t_{peak} = 1 \text{ sec.}$ )	$I_{peak}$	0.5	Amp
Power Dissipation @ $T_L = 50^\circ\text{C}$ , $L = 3/8"$ from body	$P_{tot}$	250	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	$^\circ\text{C}$

Electrical Characteristics @ 25°C*	Symbol	Absolute Limits	Unit
Breakdown Voltage @ $I_r = 0.1 \text{ mA}$	PIV	100 (Min)	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	$I_R$	0.025 (Max)	$\mu\text{A}$
Reverse Leakage ( $V_r = 20 \text{ V}$ , $150^\circ\text{C}$ )	$I_R$	50 (Max)	$\mu\text{A}$
Reverse Leakage Current @ $V_R = 75 \text{ V}$	$I_R$	5.0 (Max)	$\mu\text{A}$
Capacitance @ $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	4.0 (Max)	pF
Reverse Recovery Time (note 1)	$t_{rr}$	4.0 (Max)	nSecs
Forward Recovery Time (note 2)	$V_{fr}$	2.5 (Max)	Volts

Note 1:  $I_F = 10 \text{ mA}$ ,  $R_L = 100 \text{ Ohms}$ ,  $V_r = 6.0 \text{ Volts}$ ,  $I_{rr} = 1.0 \text{ mA}$

Note 2:  $I_F = 50 \text{ mA dc}$

**\*UNLESS OTHERWISE SPECIFIED**

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.